

**In the Claims**

Claims 1-34 (Cancelled).

35. (Currently Amended) Integrated circuitry comprising:  
a semiconductive substrate having an outer surface;  
an inner conductive core spaced from and suspended over the outer surface;  
a polymer dielectric layer surrounding a substantial portion of the inner conductive core; and  
an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer, wherein the outer conductive sheath is not formed directly on the outer surface.

36. (Currently Amended) Integrated circuitry comprising:  
a semiconductive substrate having an outer surface;  
a pair of spaced-apart terminal members disposed over the outer surface and extending elevationally away therefrom;  
an inner conductive core operably connected with and suspended between the spaced-apart terminal members above the outer surface;  
a polymer dielectric layer over a substantial portion of the inner conductive core; and  
an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer, wherein the outer conductive sheath is not formed directly on the outer surface.

37. (Currently Amended) Integrated circuitry comprising:

- a substrate having an outer surface;
- a pair of upstanding, spaced-apart conductive terminal members disposed over the substrate outer surface;
- a copper-comprising layer of material operably connected with and suspended above the outer surface between the terminal members, the copper-comprising layer having a thickness of between about 100 to 200 nanometers;
- a conductive layer of material disposed over and operably connected with the copper-comprising layer of material, the conductive layer comprising conductive material selected from the group consisting of copper, gold, nickel, cobalt and iron;
- a dielectric layer comprising parylene disposed over the conductive layer of material, the dielectric layer surrounding conductive layer portions which extend between the terminal members; and
- an outer conductive sheath of material disposed over the dielectric layer and surrounding dielectric layer portions which extend between the terminal members, wherein the outer conductive sheath is not formed directly on the outer surface.

Claim 38 (Cancelled).

Claim 39 (Cancelled).

40. (Previously Presented) The integrated circuitry of claim 35, wherein the polymer dielectric layer comprises parylene.

41. (Previously Presented) The integrated circuitry of claim 35, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

42. (Previously Presented) The integrated circuitry of claim 35, wherein the outer conductive sheath comprises aluminum.

43. (Previously Presented) The integrated circuitry of claim 35, wherein the inner conductive core comprises copper.

44. (Previously Presented) The integrated circuitry of claim 35, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

45. (Previously Presented) The integrated circuitry of claim 36, wherein the polymer dielectric layer comprises parylene.

46. (Previously Presented) The integrated circuitry of claim 36, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

47. (Previously Presented) The integrated circuitry of claim 36, wherein the outer conductive sheath comprises aluminum.

48. (Previously Presented) The integrated circuitry of claim 36, wherein the inner conductive core comprises copper.

49. (Previously Presented) The integrated circuitry of claim 36, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

50. (Currently Amended) Integrated circuitry comprising:  
a semiconductive substrate having an outer surface;  
an inner conductive core spaced from and over the outer surface;  
a polymer dielectric layer surrounding a substantial portion of the suspended inner conductive core; and

an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed directly on the outer surface.

51. (Previously Presented) The integrated circuitry of claim 50, wherein the polymer dielectric layer comprises parylene.

52. (Previously Presented) The integrated circuitry of claim 50, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

53. (Previously Presented) The integrated circuitry of claim 50, wherein the outer conductive sheath comprises aluminum.

54. (Previously Presented) The integrated circuitry of claim 50, wherein the inner conductive core comprises copper.

55. (Previously Presented) The integrated circuitry of claim 50, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

56. (Currently Amended) Integrated circuitry comprising:

- a semiconductive substrate having an outer surface;
- a pair of spaced-apart terminal members disposed over the outer surface and extending elevationally away therefrom;
- an inner conductive core operably connected with and suspended between the spaced-apart terminal members above the outer surface;
- a polymer dielectric layer surrounding the suspended inner conductive core; and
- an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer while some void space is present between the dielectric layer over the suspended inner conductive core and the outer surface, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed ~~over~~ directly on the substrate outer surface.

57. (Previously Presented) The integrated circuitry of claim 56, wherein the polymer dielectric layer comprises parylene.

58. (Previously Presented) The integrated circuitry of claim 56, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

59. (Previously Presented) The integrated circuitry of claim 56, wherein the outer conductive sheath comprises aluminum.

60. (Previously Presented) The integrated circuitry of claim 56, wherein the inner conductive core comprises copper.

61. (Previously Presented) The integrated circuitry of claim 56, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

62. (Currently Amended) Integrated circuitry comprising:

- a substrate having an outer surface;
- a pair of upstanding, spaced-apart conductive terminal members disposed over the substrate outer surface;
- a copper-comprising layer of material operably connected with and suspended above the outer surface between the terminal members, the copper-comprising layer having a thickness of between about 100 to 200 nanometers;
- a conductive layer of material operably connected with the copper-comprising layer of material and suspended above the outer surface between the terminal members, the conductive layer comprising conductive material selected from the group consisting of copper, gold, nickel, cobalt, and iron;
- a dielectric layer comprising parylene disposed over the conductive layer of material, the dielectric layer surrounding the suspended conductive layer portions; and
- an outer conductive sheath of material disposed over the dielectric layer and surrounding dielectric layer portions which extend between the terminal members, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed ~~over~~ directly on the substrate outer surface.



63. (Previously Presented) The integrated circuitry of claim 62, wherein the copper-comprising layer and the conductive layer of material operably connected with the copper comprising layer together define an inner conductive core that includes at least two different conductive materials.

Claim 64 (Cancelled).

65. (Previously Presented): The integrated circuitry of claim 62, wherein the outer conductive sheath comprises aluminum.

66. (Currently Amended) Integrated circuitry comprising:

- a semiconductive substrate having an outer surface;
- a pair of spaced-apart terminal members disposed over the outer surface and extending elevationally away therefrom;
- an inner conductive core operably connected with and suspended between the spaced-apart terminal members above the outer surface;
- a polymer dielectric layer surrounding the suspended inner conductive core; and
- an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer while some void space is present between the dielectric layer over the suspended inner conductive core and the outer surface, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed ~~over~~ directly on the substrate outer surface, wherein the void space is formed by removing masking material from elevationally below conductive material portions extending between the pair of spaced-apart terminal members.

67. (Currently Amended) Integrated circuitry comprising:  
a semiconductive substrate having an outer surface;  
an inner conductive core spaced from and suspended over the outer surface;  
a polymer dielectric layer surrounding a substantial portion of the inner conductive core; and  
an outer conductive sheath completely surrounding the polymer dielectric layer, wherein the outer conductive sheath is not directly formed on the outer surface.

Please add the following new claims:

68. (New) Integrated circuitry comprising:

a semiconductive substrate having an outer surface;  
a pair of spaced-apart terminal members disposed over the outer surface;  
an inner conductive core operably connected with and suspended between  
the spaced-apart terminal members above the outer surface;  
a polymer dielectric layer surrounding the suspended inner conductive  
core; and  
an outer conductive sheath surrounding a substantial portion of the  
polymer dielectric layer while leaving some void space between the outer  
conductive sheath and the outer surface.

69. (New) The integrated circuitry of claim 68, wherein the polymer  
dielectric layer comprises parylene.